

# Efficient light generation in TMDC with high spatial resolution using Cathodoluminescence

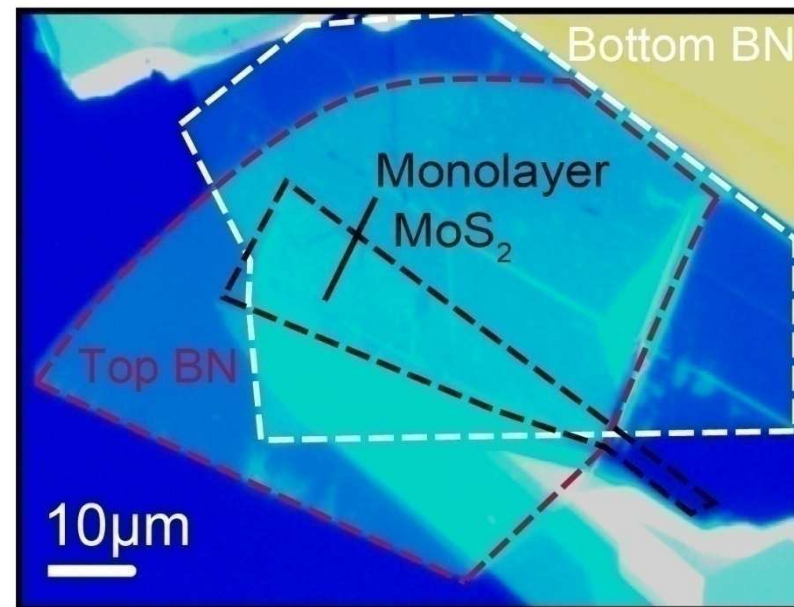
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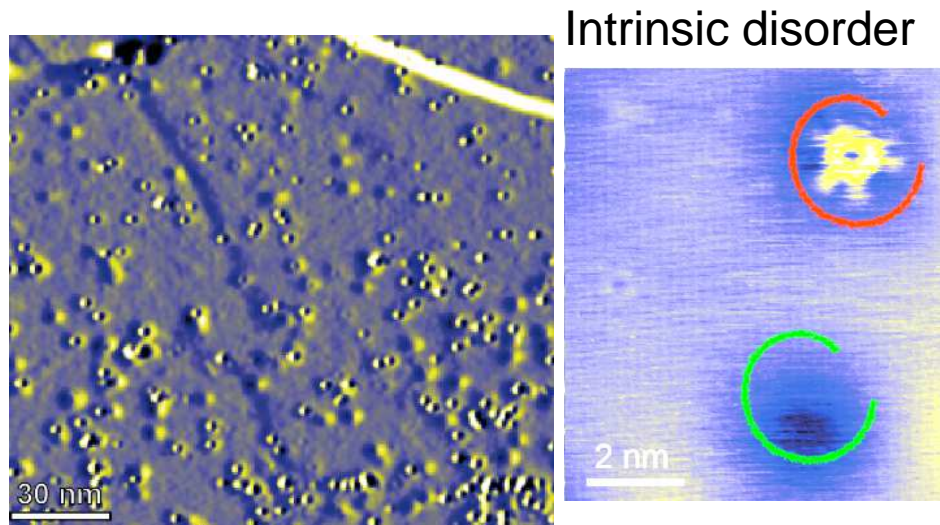
**Director: Vincent Bouchiat**

S. Lisi, W-L. Liu, F. Donatini, T. Jakubczyk, P. Stepanov, J. Kasprzak, M. Richard, J. Coraux, L. Marty, N. Bendiab, **J. Renard, V. Bouchiat**, (CNRS, Grenoble, France)

K. Watanabe, T. Taniguchi (NIMS, Japan)

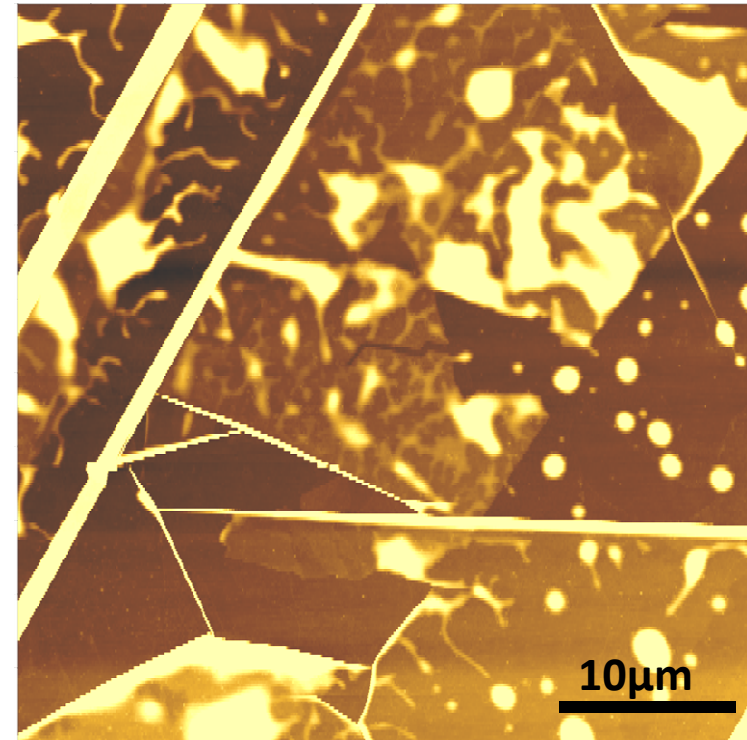


# Probing disorder in VdW heterostructures

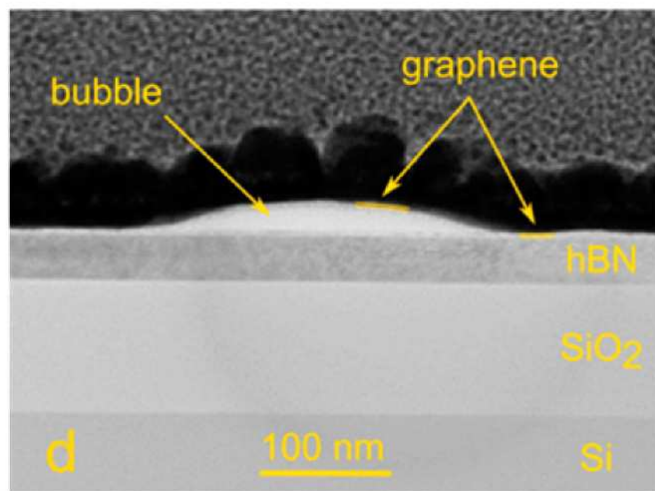


STM image of synthetic MoS<sub>2</sub>  
(Dubey et al, ACS Nano, 2017)

Extrinsic disorder (interfaces)



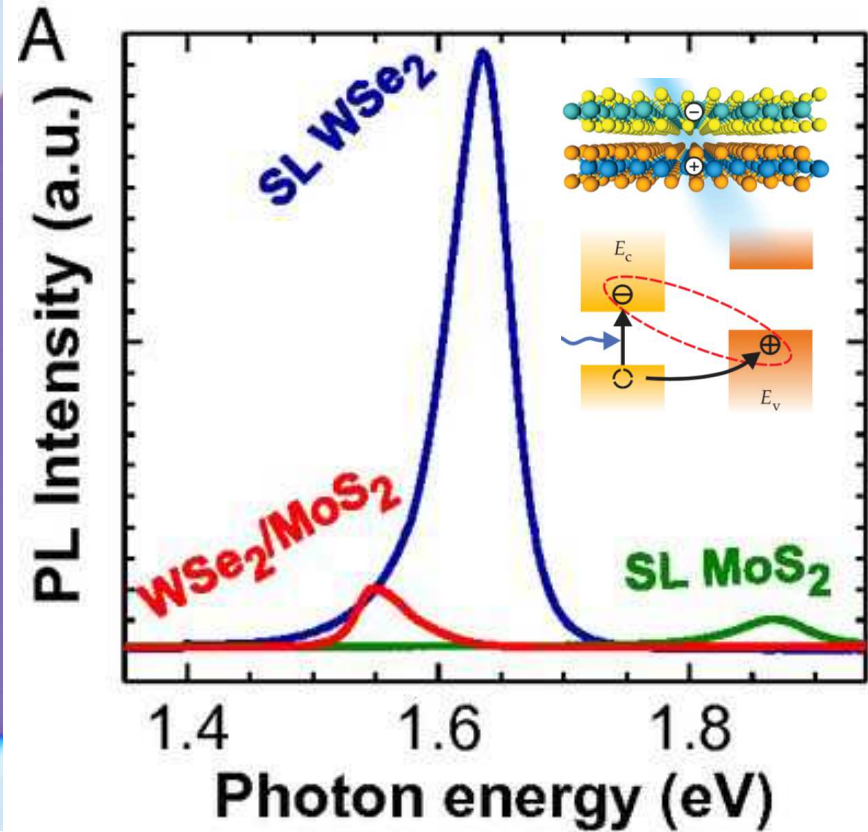
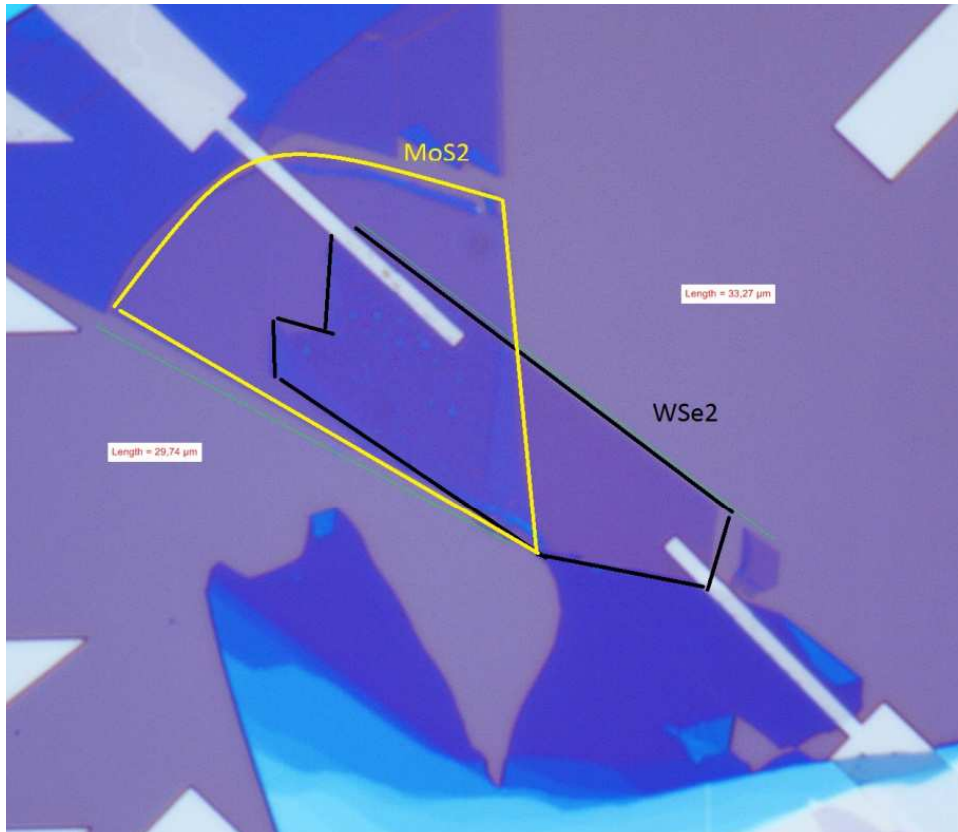
AFM image of BN encapsulated MoS<sub>2</sub>  
(showing bubbles, cracks and wrinkles)



TEM image of graphene on hBN (Kretinin et al Nano Lett., 2014)

**How do extrinsic sources of disorder affect the optoelectronic properties of TMD monolayer heterostructures ?**

# Interlayer coupling affecting PL

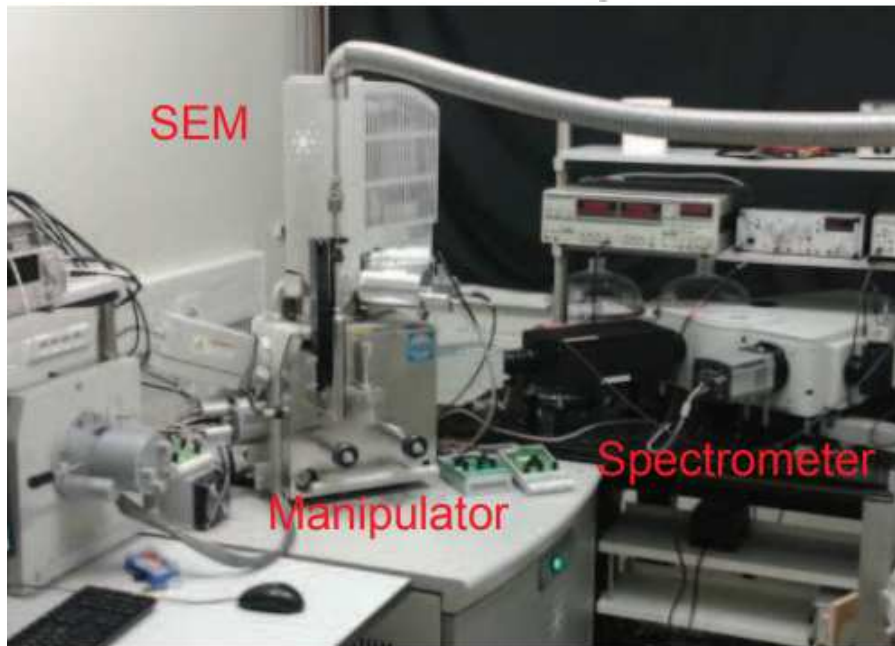
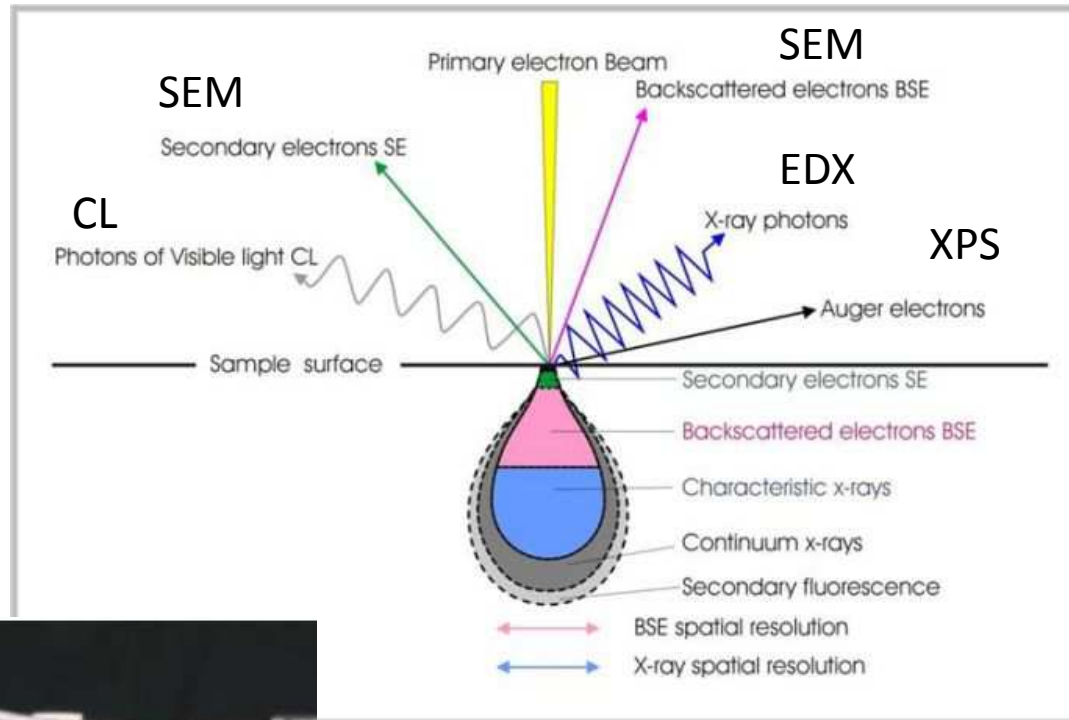


Fang, Hui, et al. PNAS 2014

Can we go below the diffraction limit in probing disorder by luminescence ?

What happens when the bubbles that are as small as 100 to 200nm??

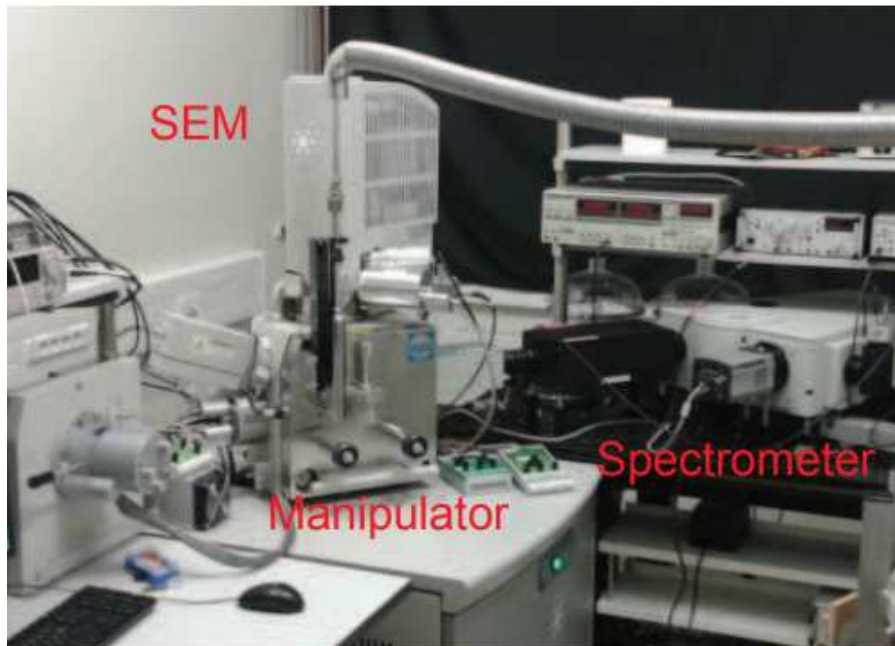
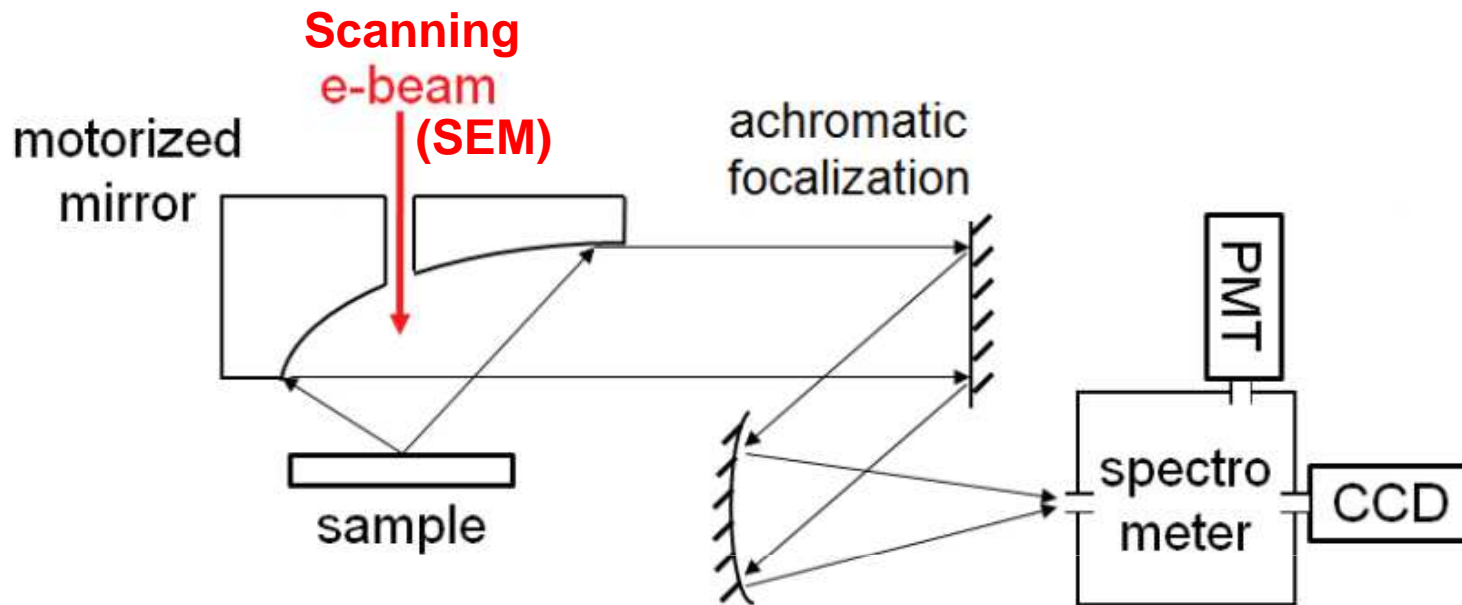
# A relevant Probe : Cathodoluminescence (CL)



Electron beam excitation

High spatial resolution ~ 10nm.

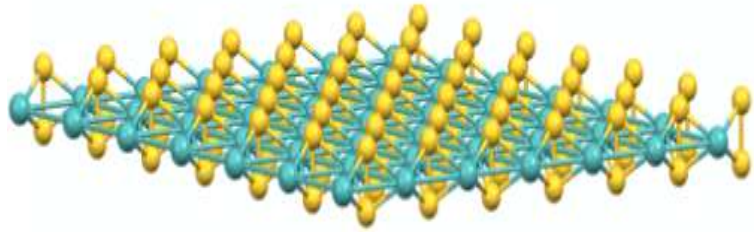
# A relevant Probe : Cathodoluminescence



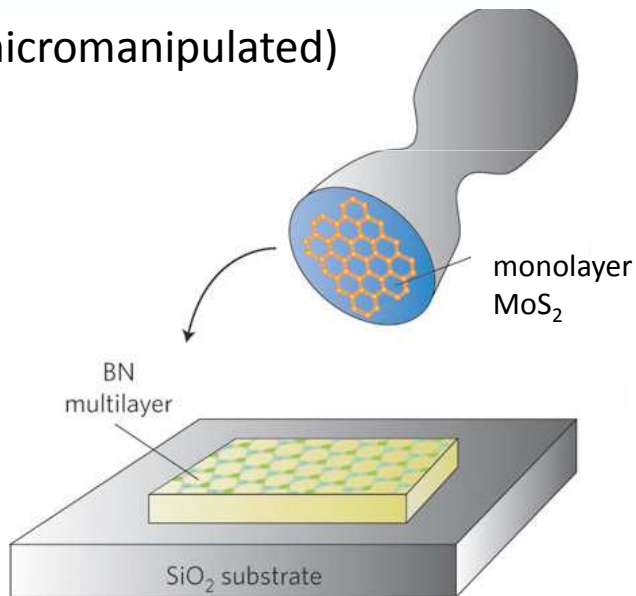
Electron beam excitation

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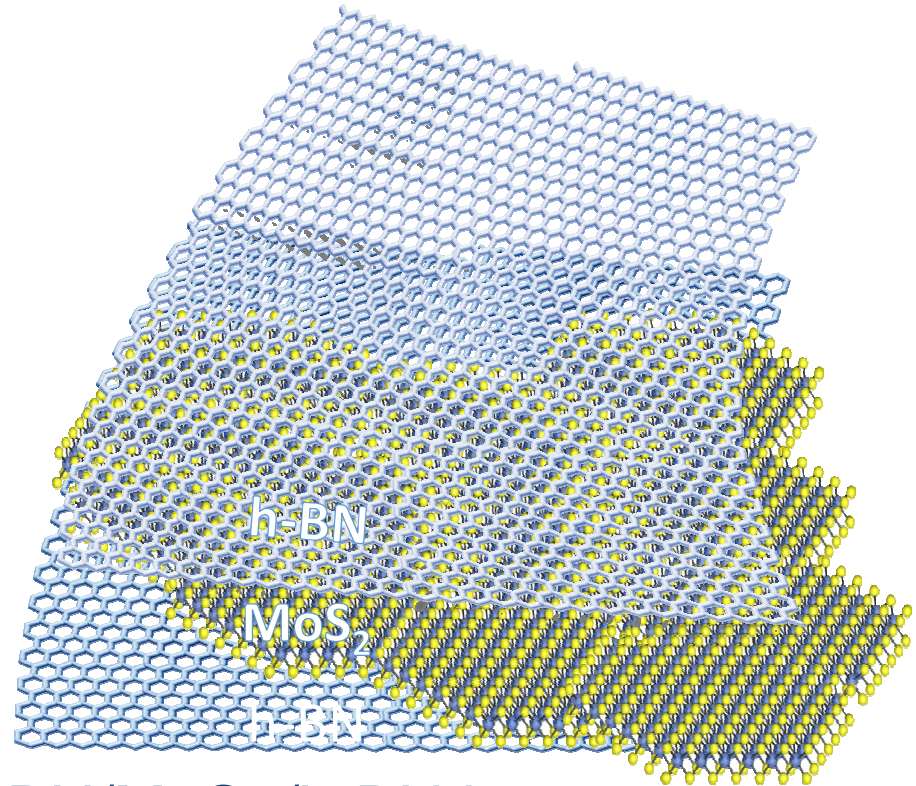
# Deterministic transfer method



Manual (micromanipulated) stamping



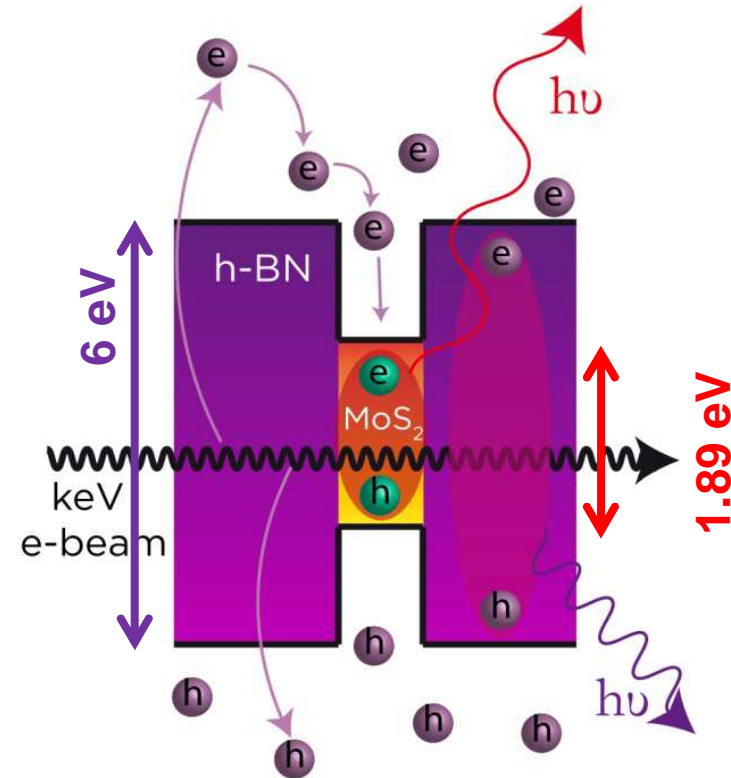
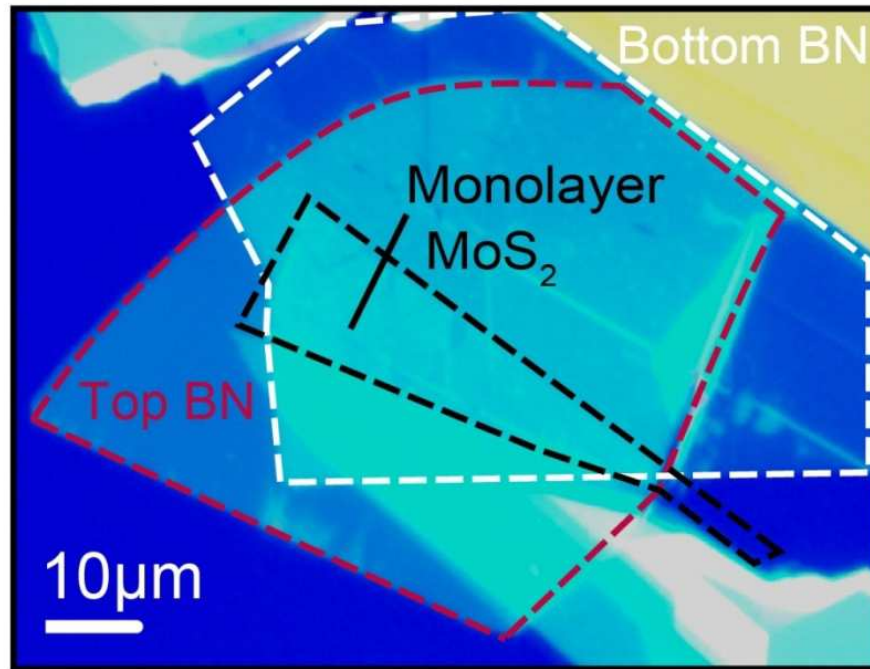
**e/h** recombination  
requires no  
phonons!  
(direct band-gap)



h-BN/MoS<sub>2</sub>/h-BN heterostructure  
PDMS Viscoelastic stamping

Castellanos –gomez et al. 2D Mater. 2014

# Cathodoluminescence with charge transfer



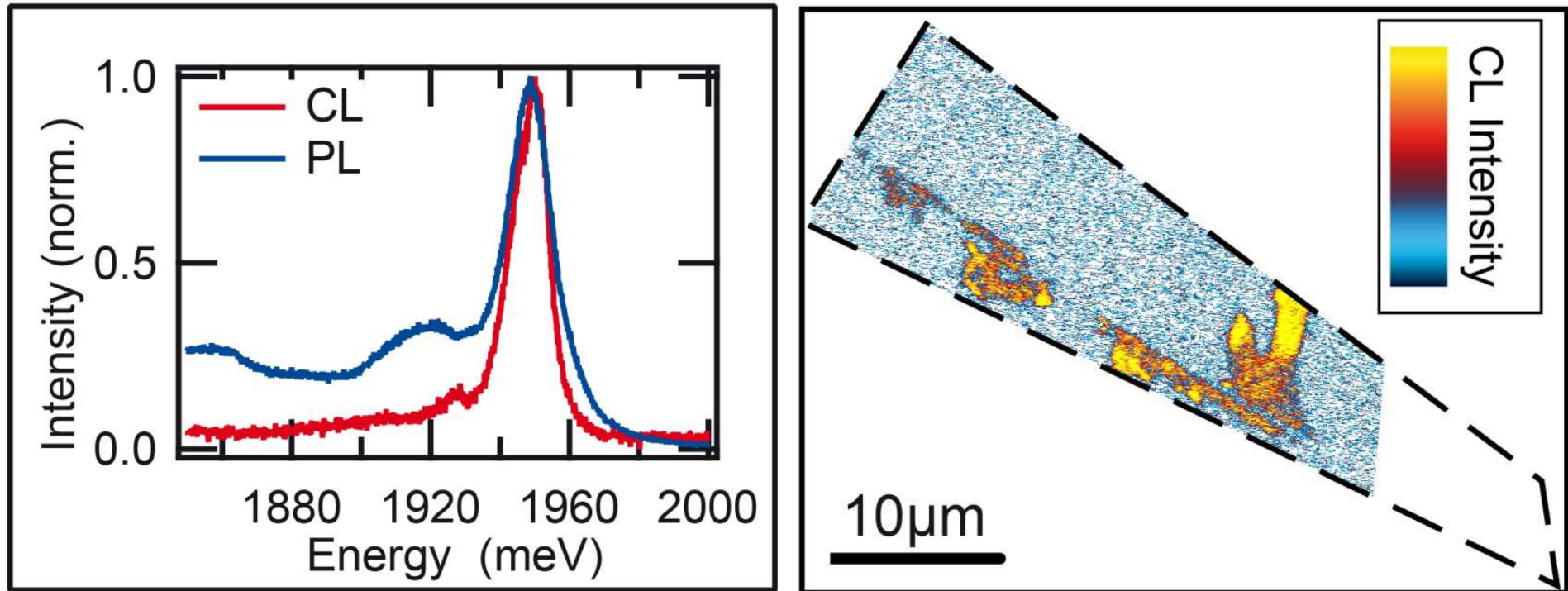
h-BN is playing two roles : protection, buffer layer AND  
Generation of e/h pairs (excitons)

Good interlayer coupling mandatory!!

Nayak et al in preparation  
(Zheng et al Nanoletters 2017)



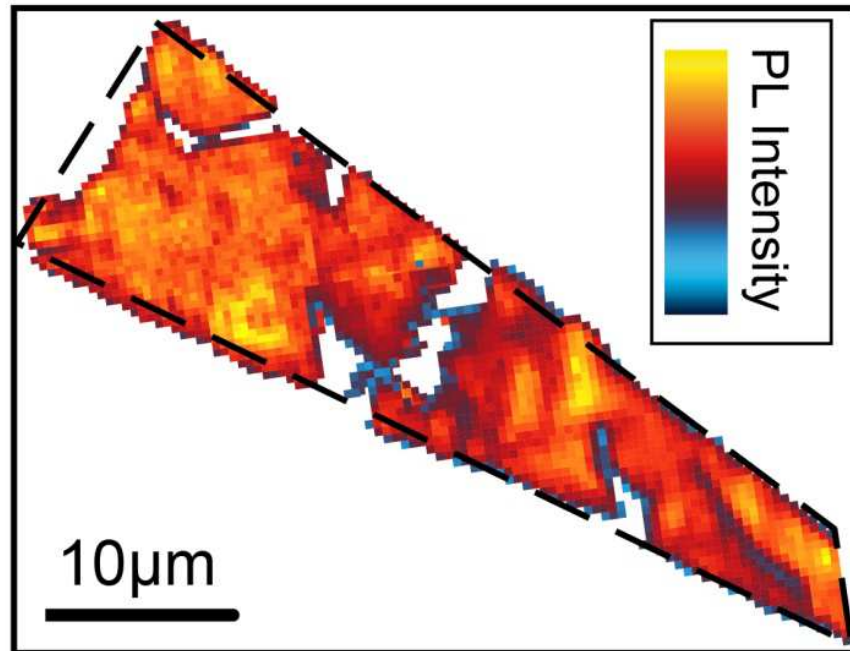
# CL mapping of the Heterostructure



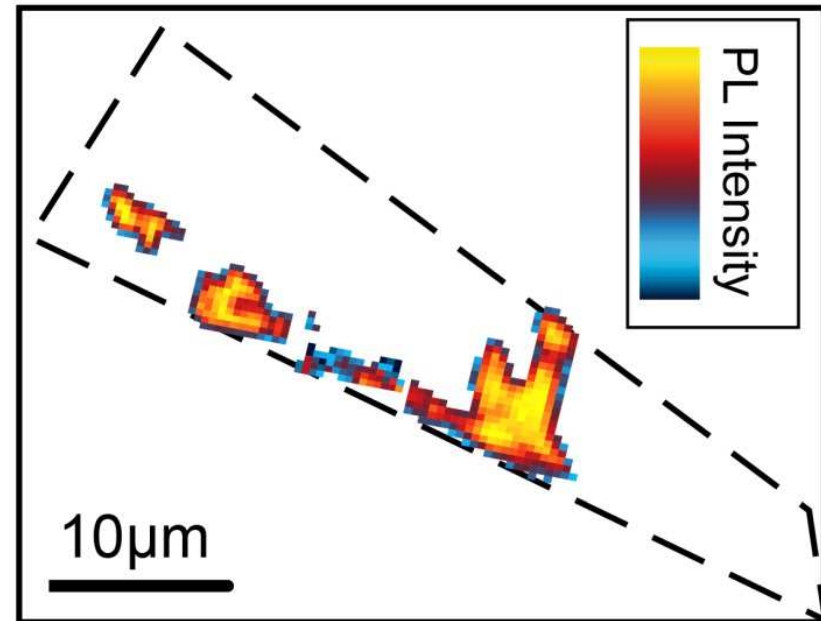
CL spectrum is sharper because the probing area is reduced and not affected by convolution with defective area

Why CL is appearing only in selective sub-regions of the heterostructure ?

# Photoluminescence mapping



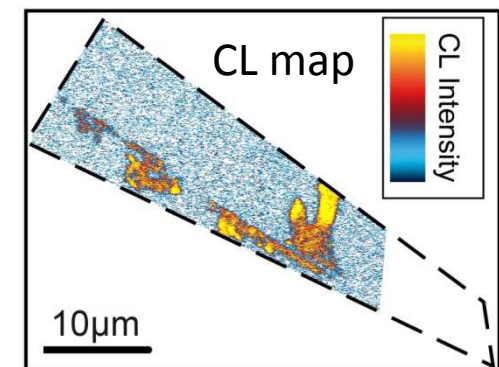
PL map before  
cathodoluminescence



PL map after  
cathodoluminescence

Interestingly the PL is quenched after SEM e-beam irradiation exactly at the zones where CL was not seen.

So CL is invasive only at specific (dirty) places only

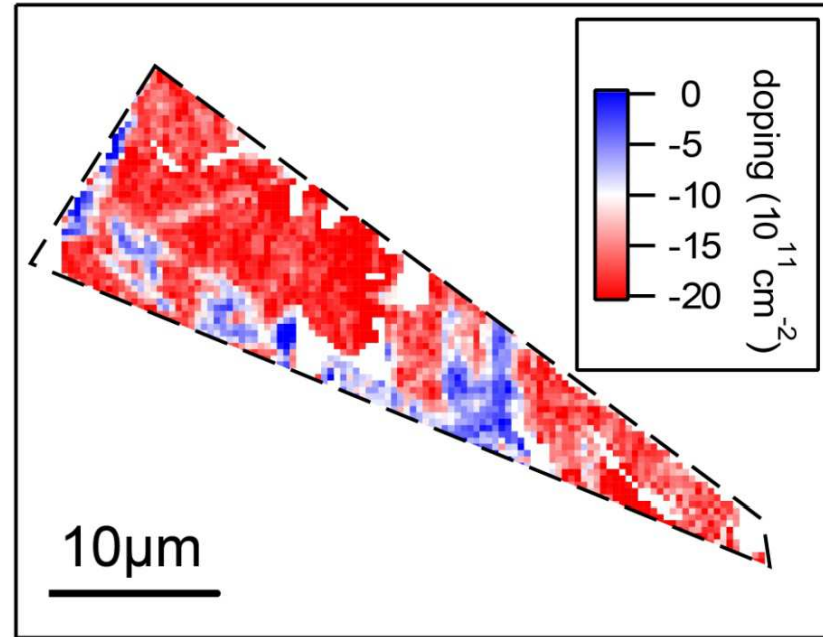
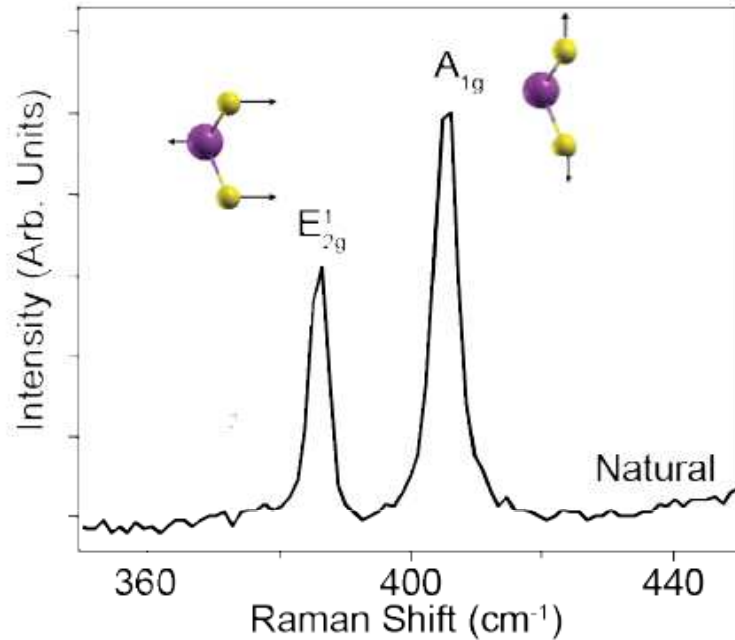


**SEM has induced further irreversible defects in the “dirty” uncoupled areas**

**Are these new defects intrinsic or extrinsic to MoS<sub>2</sub> ?**

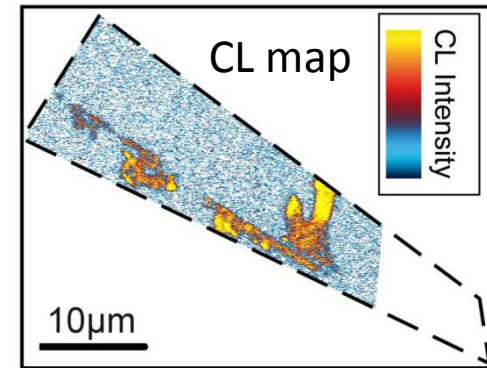
**To explore, let us perform Raman spectroscopy mappings**

# Raman mapping before CL

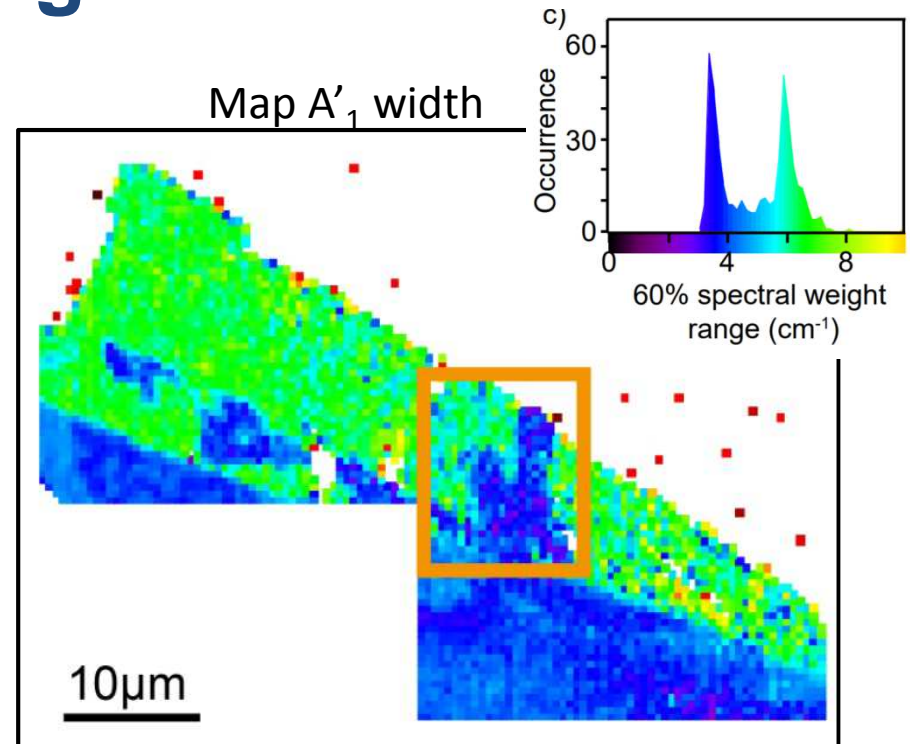
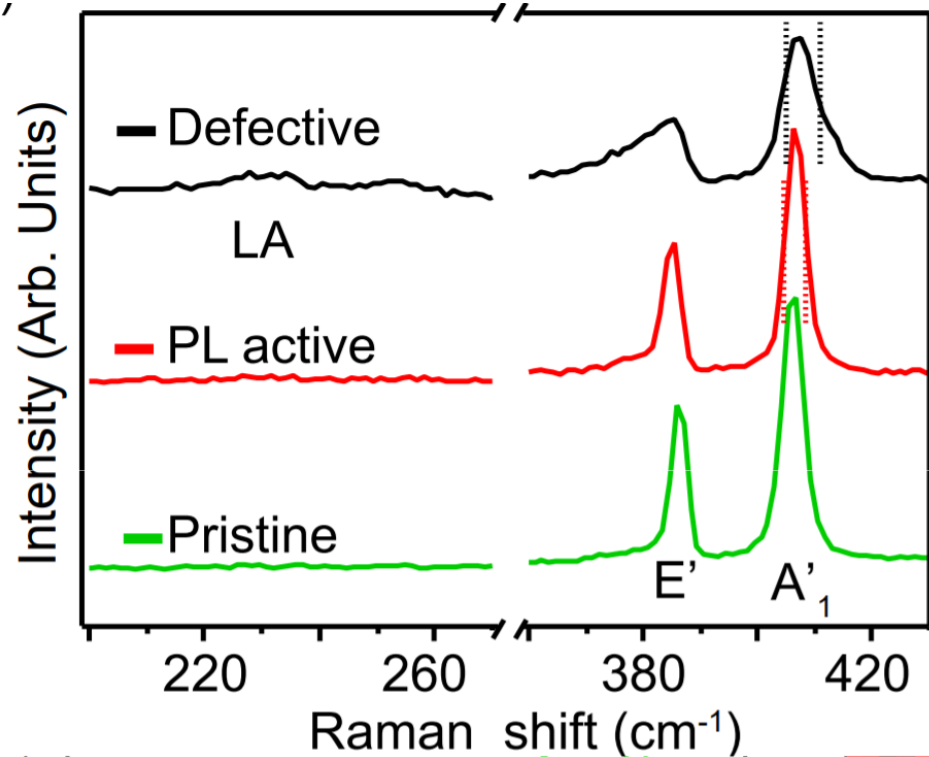


Clear correlation between coupling and doping.

Dirty areas experience high doping by the contaminants



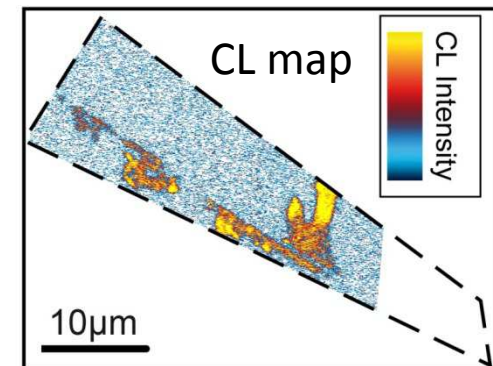
# Raman mapping after CL



Defects in PL quenched region

Broadening of Raman peaks is linked to structural defects

(Mignuzzi et al PRB 2015)



# Why defects are generated by SEM in uncoupled region?

- Threshold for knock-on  $> 10\text{keV} \gg 1\text{ keV}$
- Poor contacts  $\text{MoS}_2/\text{h-BN} \rightarrow \text{water vapour/air}$
- Volmer reaction is promoted by electron in aqueous environment
  - $\rightarrow$  possible adsorption of Hydrogen on  $\text{MoS}_2$

Xie, Junfeng, et al. *Advanced materials* 2013

Chemical reaction in uncoupled regions

# Conclusions and Outlook

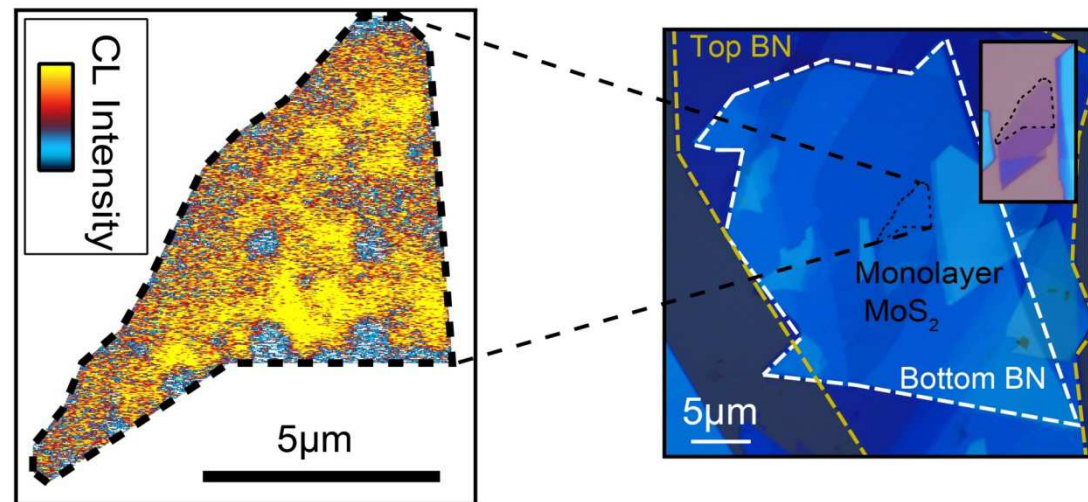
- Interlayer coupling is very important in heterostructures to harness the intrinsic property of the 2D material.
- Efficient light generation under e-beam irradiation in a VdW heterostructures with high spatial resolution (beyond diffraction limit) and also to probe disorder at nm scale level.
- Heterostructures using pickup techniques based on VdW attraction gives good homogeneous electronic coupling.

## Refs:

S.Dubey et al ACS Nano (2017)

G. Nayak et al, in preparation

T. Jakubczyk et al, in preparation



# Thanks for your attention.

